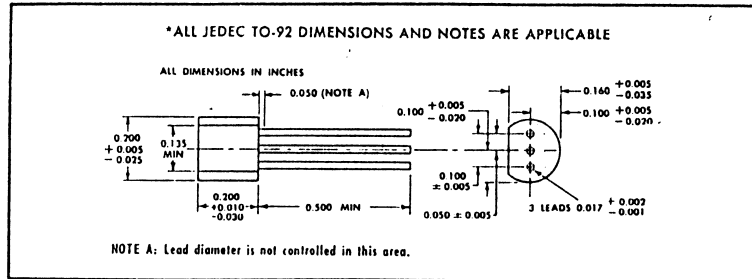


2N4997

N-P-N SILICON TRANSISTOR



\*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector-Base Voltage	30 V
Collector-Emitter Voltage (See Note 1)	18 V
Emitter-Base Voltage	4 V
Continuous Collector Current	50 mA
Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 2)	250 mW
Storage Temperature Range	-65°C to 150°C
Lead Temperature 1/16 Inch from Case for 10 Seconds	260°C

NOTES: 1. This value applies when the base-emitter diode is open-circuited.  
 2. Derate linearly to 150°C free-air temperature at the rate of 2 mW/deg.  
 \*Indicates JEDEC registered data

\*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CBO}$ Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	30			V
$V_{(BR)CEO}$ Collector-Emitter Breakdown Voltage	$I_C = 2 mA, I_B = 0$ , See Note 3	18			V
$V_{(BR)EBO}$ Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4			V
$I_{CBO}$ Collector Cutoff Current	$V_{CB} = 15 V, I_E = 0$ $V_{CE} = 15 V, I_E = 0, T_A = 85^\circ C$			100	nA
$h_{FE}$ Static Forward Current Transfer Ratio	$V_{CE} = 10 V, I_C = 2 mA$	30		150	
$ h_{fe} $ Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = 10 V, I_C = 2 mA, f = 100 MHz$	6		14	
$ y_{fe} $ Small-Signal Common-Emitter Forward Transfer Admittance	$V_{CE} = 10 V, I_C = 2 mA, f = 10 MHz$		70		mmho
$C_{cb}$ Collector-Base Capacitance	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$ , See Note 4	0.1		0.65	pF
$r_{out}$ Parallel-Equivalent Common-Emitter Short-Circuit Output Resistance	$V_{CE} = 10 V, I_C = 2 mA, f = 10 MHz$	50			kΩ
$r_b, C_c$ Collector-Base Time Constant	$V_{CB} = 10 V, I_E = -2 mA, f = 79.8 MHz$		14	20	ps

operating characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	TYP	UNIT
NF Spot Noise Figure	$V_{CE} = 10 V, I_C = 2 mA, R_G = 100 \Omega, f = 100 MHz$	2.5	dB

\*Indicates JEDEC registered data (typical data excluded)

